

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims 1-10:

Claims 1-4 (Canceled)

5. (Currently Amended) A semiconductor epitaxial wafer having ~~an~~ plural epitaxial ~~layer~~ layers stacked on a semiconductor substrate, wherein:

the semiconductor substrate is doped with nitrogen;

the plural epitaxial layers are stacked on a front side of the semiconductor substrate; and

an impurity concentration of any one of the plural epitaxial layers is high enough to afford a latch-up resistance and a high-frequency conformity and is higher than impurity concentrations of the semiconductor substrate and other ones of the plural epitaxial layers.

6. (Currently Amended) A semiconductor epitaxial wafer having ~~an~~ plural epitaxial ~~layer~~ layers stacked on a semiconductor substrate, wherein:

the semiconductor substrate is doped with nitrogen;

the plural epitaxial layers are stacked on a front side of the semiconductor substrate;

an impurity concentration of any one of the plural epitaxial layers is high enough for the formation of a gettering site and is higher than impurity concentrations of the semiconductor substrate and other ones of the plural epitaxial layers; and

an impurity concentration of the semiconductor substrate is at a level of suppressing impurity discharge from the semiconductor substrate.

7. (Previously Presented) The semiconductor epitaxial wafer according to claim 5 or 6, wherein an impurity concentration of the epitaxial layer being in contact with the semiconductor substrate among the plural epitaxial layers is higher than the impurity concentrations of the semiconductor substrate and the other epitaxial layers.

8. (Currently Amended) A semiconductor epitaxial wafer having ~~an~~ plural epitaxial ~~layer~~ layers stacked on a semiconductor substrate, wherein:

the semiconductor substrate is doped with nitrogen;

the plural epitaxial layers are stacked on a front side of the semiconductor substrate;

an impurity concentration of a high-concentration epitaxial layer among the plural epitaxial layers is 2.77×10^{17} to 5.49×10^{19} (atoms/cm³); and

an impurity concentration of the semiconductor substrate is 1.33×10^{14} to 1.46×10^{16} (atoms/cm³).

9. (Currently Amended) A semiconductor epitaxial wafer having ~~an~~ plural epitaxial ~~layer~~ layers stacked on a semiconductor substrate, wherein:

the semiconductor substrate is doped with nitrogen;

the plural epitaxial layers are stacked on a front side of the semiconductor substrate;

a resistivity of a high-concentration epitaxial layer among the plural epitaxial layers is 0.002 to 0.1 ($\Omega \cdot \text{cm}$); and

a resistivity of the semiconductor substrate is 1 to 100 ($\Omega \cdot \text{cm}$).

10. (Previously Presented) The semiconductor epitaxial wafer according to any one of claims 5 to 9, wherein a high-concentration epitaxial layer among the plural epitaxial layers contains boron.